

Analog Circuit Session 2

Oct. 23, 2020 15:45 - 16:00

Improved Nagata Current Source Insensitive to Temperature and Power Supply Voltage

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ASO Corp.



- Research Background and Objective
- Original Nagata Current Source
- Improvement to Supply Voltage Insensitivity
- Improvement to Temperature Insensitivity
- Simulation Verification
- Conclusion



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Research Background





Research Objective

Improvement of Nagata current source insensitive to temperature as well as supply voltage





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Original Nagata Current Source



Nagata current source

[1] Inventor M. Nagata, Japanese Patent, Showa 46-16463 (Dec. 12, 1966)



At peak vicinity

Small *l*OUT change against *VDD* change



Widely used. Ex: in DC-DC converter IC



Reason for having a peak (1)





Reason for having a peak (2)





Improvement to Widen Flat Range





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Widened Flat Range



[2] M. Hirano, N. Tsukiji, H. Kobayashi, "Simple Reference Current Source Insensitive to Power Supply Voltage Variation - Improved Minoru Nagata Current Source", IEEE 13th International Conference on Solid-State and Integrated Circuit Technology, Hangzhou, China (Oct. 2016)



Measurements of Supply Voltage Sensitivity



Total output current is constant against VDD variation

[3] M. Hirano, N. Kushita, Y. Moroshima, H. Harakawa, T. Oikawa, N. Tsukiji, T. Ida, Y. Shibasaki, H. Kobayashi, "Silicon Verification of Improved Nagata Current Mirrors", IEEE 14th International Conference on Solid-State and Integrated Circuit Technology, Qingdao, China (Nov. 2018)



ISOCC 2020

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MOSFET Temperature Characteristics





Proposed Reference Current Source





Comparison



Insensitive to supply voltage





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SPICE Simulation Circuit



W/L, R values are designed to make *l*out temperature-, supply voltage-insensitive.

LTspice TSMC 0.18µm MOS model



Simulation for Supply Voltage





Simulation Result for Temperature





Analysis: M2 drain current



Negative temperature characteristics



Analysis: M3 drain current



Negative temperature characteristics



Analysis: M4 drain current



Positive temperature characteristics



Analysis: M5 drain current



Positive temperature characteristics



Reason for Temperature Insensitivity





Resistor Temperature Coefficient





Point of Our Temperature Compensation



Conventional circuit



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Conclusion

- Proposal of MOS reference current sources
- Temperature insensitivity has been improved.
- Comparison

Circuit	Current constant range	Temperature
Original Nagata current source	Fair	Fair
Previously improved circuit	Excellent	Fair
Proposed circuit today	Excellent	Good